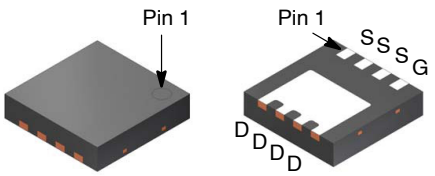
# MOSFET – N-Channel, Shielded Gate POWERTRENCH®

## 80 V, 66 A, 7 mΩ

# FDMC007N08LC




**WDFN8 3.3x3.3, 0.65P**
**(Power 33)**
**CASE 483AW**

### General Description

This N−Channel MV MOSFET is produced using **onsemi**'s advanced POWERTRENCH process that incorporates Shielded Gate technology. This process has been optimized to minimise on−state resistance and yet maintain superior switching performance with best in class soft body diode.

### Features

- Shielded Gate MOSFET Technology
- Max $R_{DS(on)}$ = 7.0 mΩ at $V_{GS}$ = 10 V, $I_D$ = 21 A
- Max $R_{DS(on)}$ = 10.4 mΩ at $V_{GS}$ = 4.5 V, $I_D$ = 17 A
- 5 V Drive Capable
- 50% Lower Qrr than Other MOSFET Suppliers
- Lowers Switching Noise/EMI
- MSL1 Robust Package Design
- 100% UIL Tested
- This Device is Pb−Free, Halide Free and RoHS Compliant

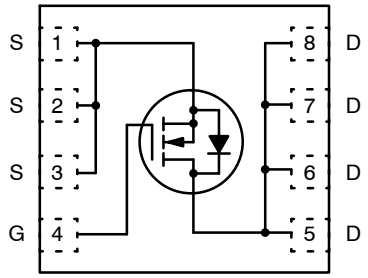
### Applications

- Primary DC−DC MOSFET
- Synchronous Rectifier in DC−DC and AC−DC
- Motor Drive
- Solar

### MARKING DIAGRAM

| | |
|---|---|
| Z | = Assembly Plant Code |
| X | = Year Code |
| YY | = Two−digit Weekly Numeric Code |
| KK | = Two−digit Alphanumeric Lot Code |
| FDMC 007N08LC | = Specific Device Code |

### PIN CONNECTIONS




### ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

### ABSOLUTE MAXIMUM RATINGS ($T_A$ = 25°C unless otherwise noted)

| Symbol | Parameter | | Value | Unit |
|---|---|---|---|---|
| $V_{DS}$ | Drain to Source Voltage | | 80 | V |
| $V_{GS}$ | Gate to Source Voltage | | ±20 | V |
| $I_D$ | Drain Current<br>– Continuous (Note 5)<br>– Continuous (Note 5)<br>– Continuous (Note 1a)<br>– Pulsed (Note 4) | <br>$T_C$ = 25°C<br>$T_C$ = 100°C<br>$T_A$ = 25°C | <br>66<br>42<br>14<br>330 | A |
| $E_{AS}$ | Single Pulse Avalanche Energy (Note 3) | | 150 | mJ |
| $P_D$ | Power Dissipation<br>Power Dissipation (Note 1a) | $T_C$ = 25°C<br>$T_A$ = 25°C | 57<br>2.4 | W |
| $T_J$, $T_{STG}$ | Operating and Storage Junction Temperature Range | | −55 to +150 | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

© Semiconductor Components Industries, LLC, 2016

## THERMAL CHARACTERISTICS

| Symbol | Parameter | Value | Unit |
|---|---|---|---|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case | 2.2 | °C/W |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient (Note 1a) | 53 | |

## ELECTRICAL CHARACTERISTICS ($T_J$ = 25°C unless otherwise noted)

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| **OFF CHARACTERISTICS** | | | | | | |
| $BV_{DSS}$ | Drain to Source Breakdown Voltage | $I_D$ = 250 μA, $V_{GS}$ = 0 V | 80 | – | – | V |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | $I_D$ = 250 μA, referenced to 25°C | – | 45 | – | mV/°C |
| $I_{DSS}$ | Zero Gate Voltage Drain Current | $V_{DS}$ = 64 V, $V_{GS}$ = 0 V | – | – | 1 | μA |
| $I_{GSS}$ | Gate to Source Leakage Current | $V_{GS}$ = ±20 V, $V_{DS}$ = 0 V | – | – | 100 | nA |
| **ON CHARACTERISTICS** | | | | | | |
| $V_{GS(th)}$ | Gate to Source Threshold Voltage | $V_{GS}$ = $V_{DS}$, $I_D$ = 120 μA | 1.0 | 1.5 | 2.5 | V |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate to Source Threshold Voltage Temperature Coefficient | $I_D$ = 120 μA, referenced to 25°C | – | –5.4 | – | mV/°C |
| $R_{DS(on)}$ | Static Drain to Source On Resistance | $V_{GS}$ = 10 V, $I_D$ = 21 A | – | 5.7 | 7.0 | mΩ |
| | | $V_{GS}$ = 4.5 V, $I_D$ = 17 A | – | 8.3 | 10.4 | |
| | | $V_{GS}$ = 10 V, $I_D$ = 21 A, $T_J$ = 125°C | – | 9.9 | 12.2 | |
| $g_{FS}$ | Forward Transconductance | $V_{DD}$ = 5 V, $I_D$ = 21 A | – | 80 | – | S |
| **DYNAMIC CHARACTERISTICS** | | | | | | |
| $C_{iss}$ | Input Capacitance | $V_{DS}$ = 40 V, $V_{GS}$ = 0 V, f = 1 MHz | – | 2100 | 2940 | pF |
| $C_{oss}$ | Output Capacitance | | – | 506 | 710 | pF |
| $C_{rss}$ | Reverse Transfer Capacitance | | – | 18 | 30 | pF |
| $R_g$ | Gate Resistance | | 0.1 | 0.4 | 0.8 | Ω |
| **SWITCHING CHARACTERISTICS** | | | | | | |
| $t_{d(on)}$ | Turn–On Delay Time | $V_{DD}$ = 40 V, $I_D$ = 21 A, $V_{GS}$ = 10 V, $R_{GEN}$ = 6 Ω | – | 10 | 20 | ns |
| $t_r$ | Rise Time | | – | 2.4 | 10 | ns |
| $t_{d(off)}$ | Turn–Off Delay Time | | – | 24 | 39 | ns |
| $t_f$ | Fall Time | | – | 2.1 | 10 | ns |
| $Q_g$ | Total Gate Charge | $V_{GS}$ = 0 V to 10 V, $V_{DD}$ = 40 V, $I_D$ = 21 A | – | 29 | 41 | nC |
| | | $V_{GS}$ = 0 V to 4.5 V, $V_{DD}$ = 40 V, $I_D$ = 21 A | – | 14 | 19 | |
| $Q_{gs}$ | Gate to Source Charge | $V_{DD}$ = 40 V, $I_D$ = 21 A | – | 5 | – | nC |
| $Q_{gd}$ | Gate to Drain “Miller” Charge | | – | 3 | – | nC |
| $Q_{oss}$ | Output Charge | $V_{DD}$ = 40 V, $V_{GS}$ = 0 V | – | 30 | – | nC |
| $Q_{sync}$ | Total Gate Charge Sync. | $V_{DS}$ = 0 V, $I_D$ = 21 A | – | 27 | – | nC |

**ELECTRICAL CHARACTERISTICS** ($T_J$ = 25°C unless otherwise noted)

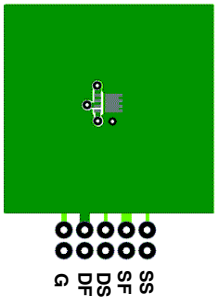
**DRAIN−SOURCE DIODE CHARACTERISTICS**

| | | | | | | |
|---|---|---|---|---|---|---|
| $V_{SD}$ | Source to Drain Diode Forward Voltage | $V_{GS}$ = 0 V, $I_S$ = 2 A (Note 2) | 0.1 | 0.7 | 1.2 | V |
| | | $V_{GS}$ = 0 V, $I_S$ = 21 A (Note 2) | 0.1 | 0.8 | 1.3 | |
| $t_{rr}$ | Reverse Recovery Time | $I_F$ = 10 A, di/dt = 300 A/μs | – | 20 | 32 | ns |
| $Q_{rr}$ | Reverse Recovery Charge | | – | 27 | 43 | nC |
| $t_{rr}$ | Reverse Recovery Time | $I_F$ = 10 A, di/dt = 1000 A/μs | – | 14 | 22 | ns |
| $Q_{rr}$ | Reverse Recovery Charge | | – | 62 | 99 | nC |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NOTES:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in$^2$ pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR−4 material. $R_{\theta CA}$ is determined by the user's board design.




a) 53°C/W when mounted on a 1 in$^2$ pad of 2 oz copper

b) 125°C/W when mounted on a minimum pad of 2 oz copper

2. Pulse Test: Pulse Width < 300 μs, Duty Cycle < 2.0%.
3. $E_{AS}$ of 150 mJ is based on starting $T_J$ = 25°C, L = 3 mH, $I_{AS}$ = 10 A, $V_{DD}$ = 80 V, $V_{GS}$ = 10 V. 100% test at L = 0.1 mH, $I_{AS}$ = 33 A.
4. Pulsed Id please refer to Figure 11 SOA graph for more details.
5. Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro−mechanical application board design.

## TYPICAL CHARACTERISTICS ($T_J$ = 25°C unless otherwise noted)

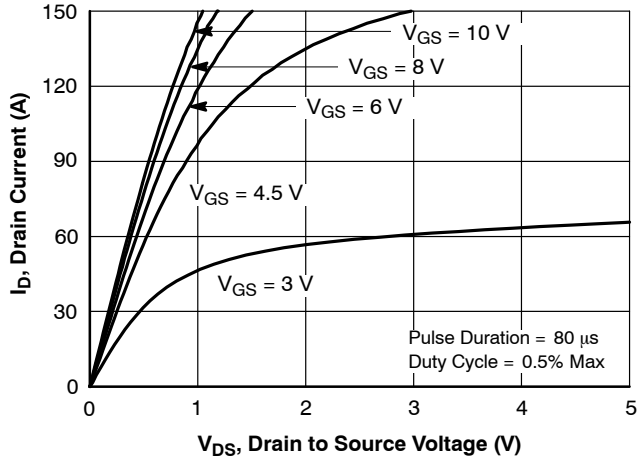



**Figure 1. On Region Characteristics**

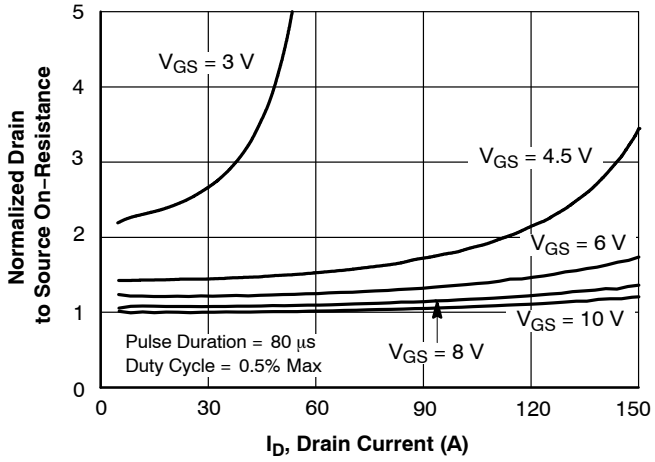



**Figure 2. Normalized On−Resistance vs. Drain Current and Gate Voltage**

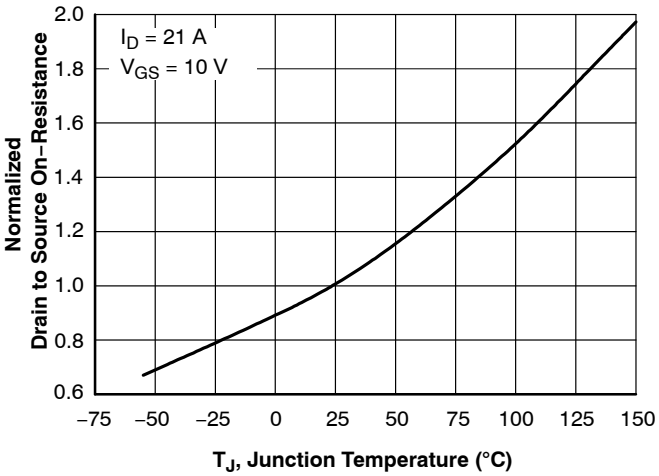



**Figure 3. Normalized On Resistance vs. Junction Temperature**

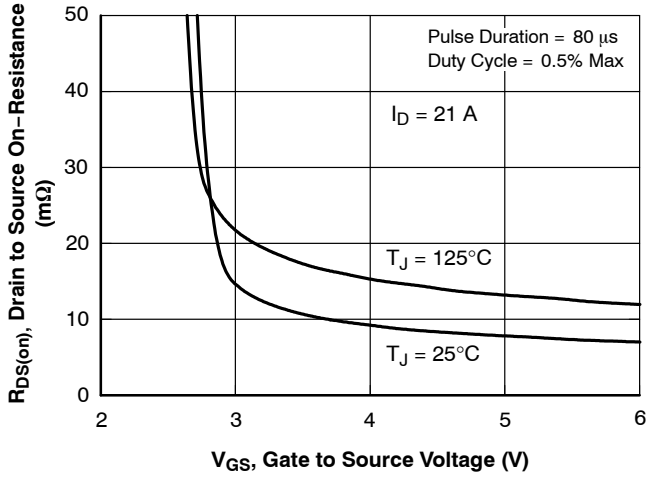



**Figure 4. On−Resistance vs. Gate to Source Voltage**

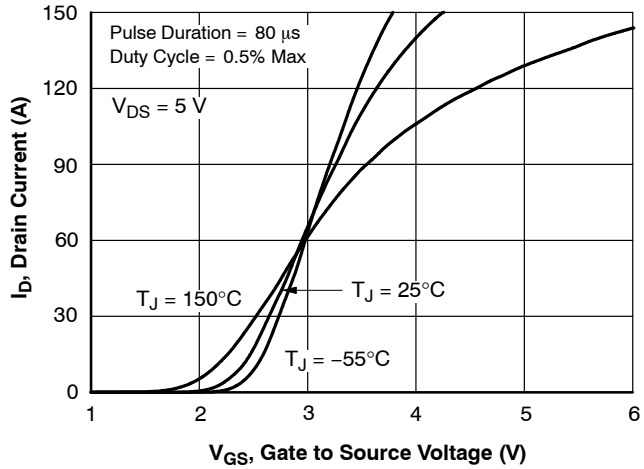



**Figure 5. Transfer Characteristics**

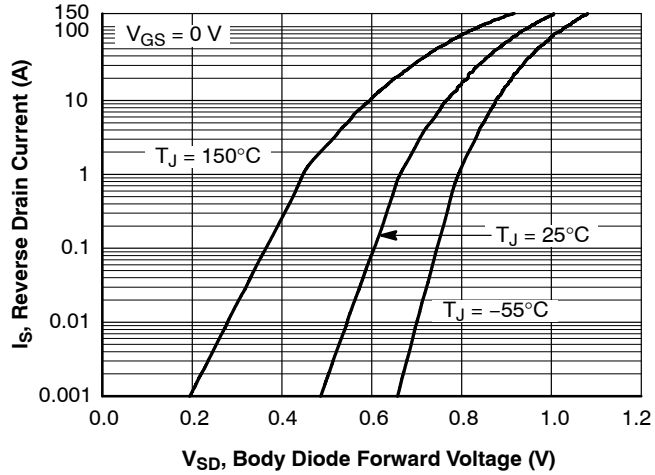



**Figure 6. Source to Drain Diode Forward Voltage vs. Source Current**

**TYPICAL CHARACTERISTICS** ($T_J$ = 25°C unless otherwise noted) (continued)

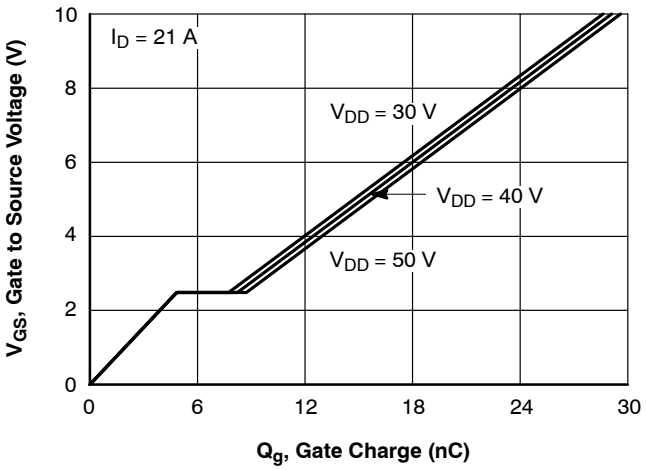



**Figure 7. Gate Charge Characteristics**

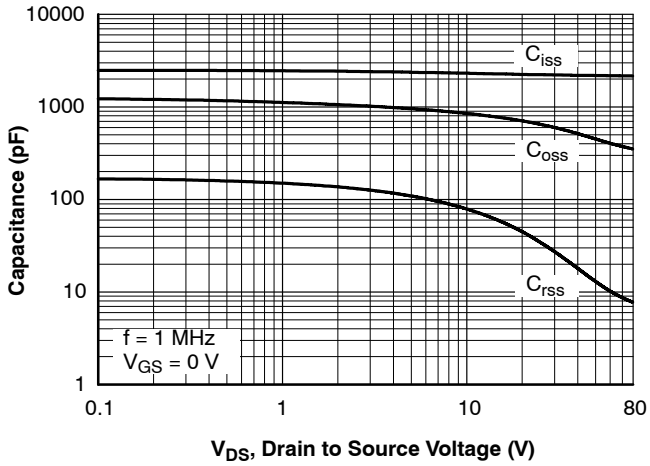



**Figure 8. Capacitance vs. Drain to Source Voltage**

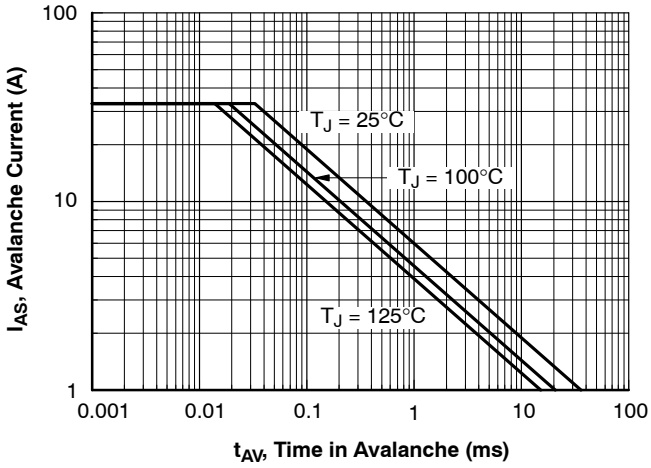



**Figure 9. Unclamped Inductive Switching Capability**

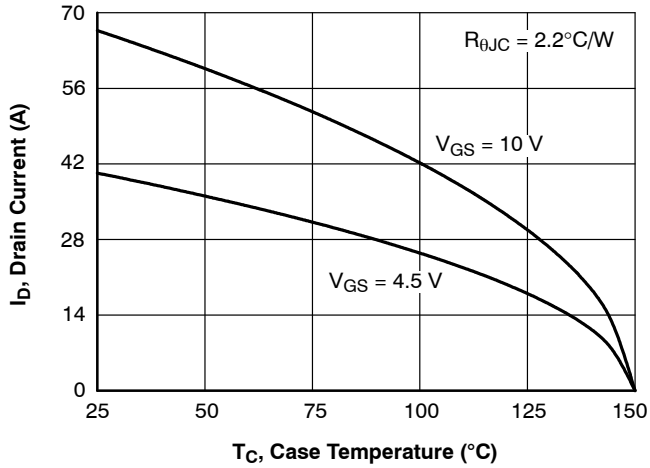



**Figure 10. Maximum Continuous Drain Current vs. Case Temperature**

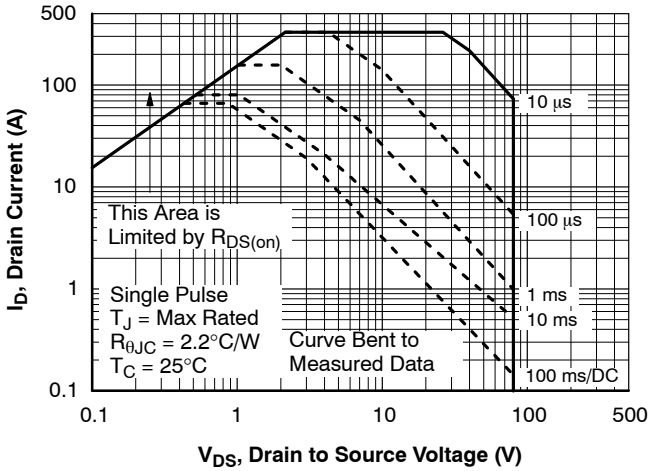



**Figure 11. Forward Bias Safe Operating Area**

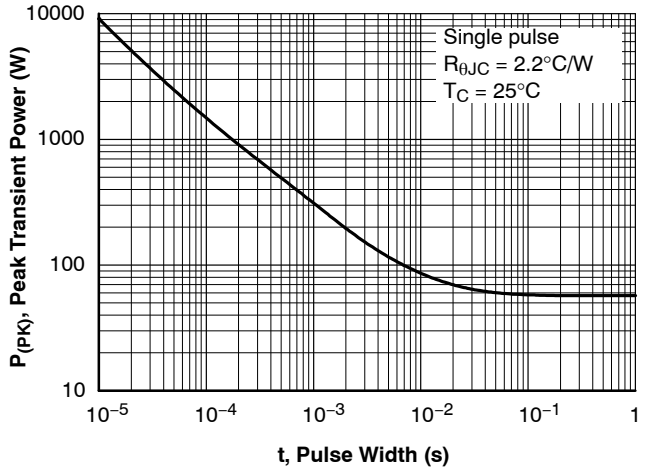



**Figure 12. Single Pulse Maximum Power Dissipation**

**TYPICAL CHARACTERISTICS** ($T_J$ = 25°C unless otherwise noted) (continued)

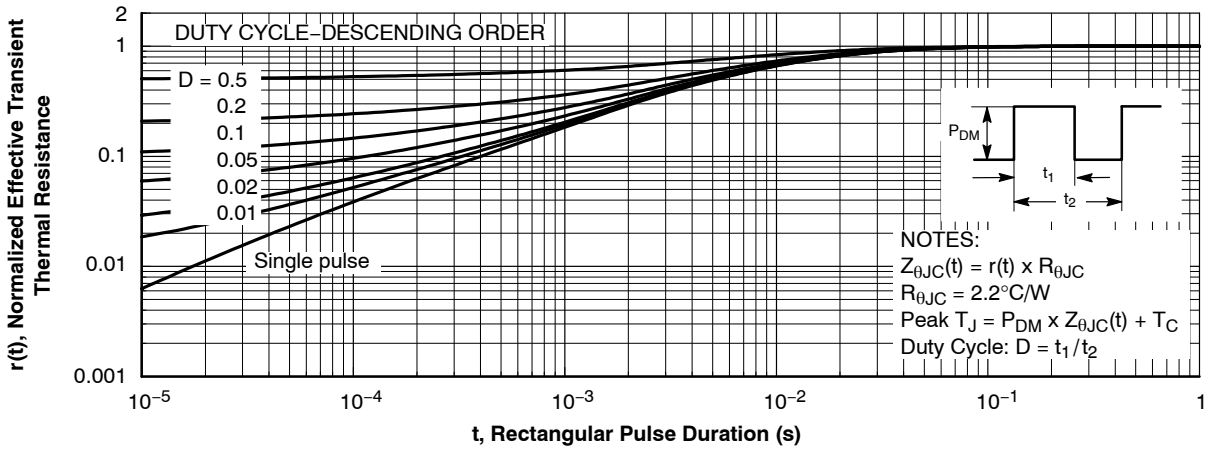


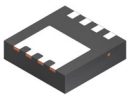

**Figure 13. Junction−to−Case Transient Thermal Response Curve**

## PACKAGE MARKING AND ORDERING INFORMATION

| Device | Device Marking | Package Type | Reel Size | Tape Width | Shipping† |
|---|---|---|---|---|---|
| FDMC007N08LC | FDMC007N08LC | WDFN8 3.3x3.3, 0.65P (Power 33) (Pb−Free) | 13” | 12 mm | 3000 / Tape & Reel |

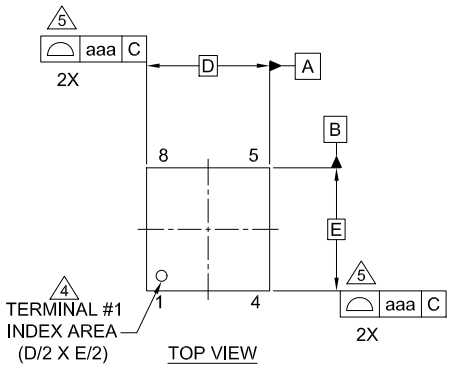
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

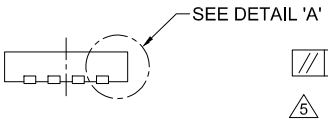
POWERTRENCH is a registered trademark of Semiconductor Components Industries, LLC dba “**onsemi**” or its affiliates and/or subsidiaries in the United States and/or other countries.



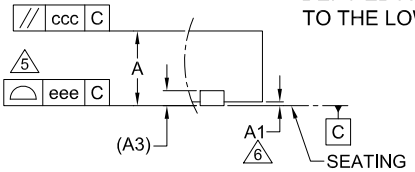
**WDFN8 3.30x3.30x0.75, 0.65P**
CASE 483AW
ISSUE B

DATE 22 MAR 2024

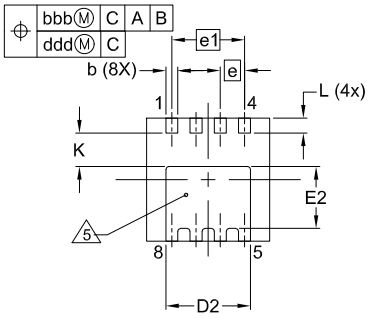



FRONT VIEW

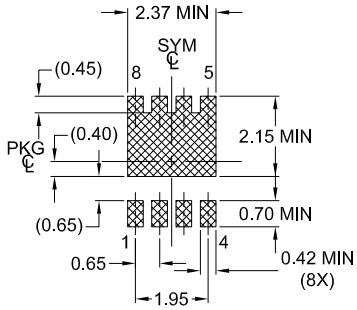



DETAIL A
SCALE: 2x




BOTTOM VIEW

## LAND PATTERN RECOMMENDATION




*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
2. ALL DIMENSIONS ARE IN MILLIMETERS.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
4. THE TERMINAL #1 IDENTIFIER AND TERMINAL NUMBERING CONVENTION SHALL CONFORM TO JEP95 SEC. 3 SPP-12. DETAILS OF TERMINAL #1 IDENTIFIER ARE OPTIONAL, BUT MUST BE LOCATED WITHIN THE ZONE INDICATED. THE TERMINAL #1 IDENTIFIER MAY BE EITHER A MOLD, EMBEDDED METAL OR MARKED FEATURE.
5. COPLANARITY APPLIES TO THE EXPOSED PADS AS WELL AS THE TERMINALS.
6. SEATING PLANE IS DEFINED BY THE TERMINALS. 'A1' IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.

| DIM | MILLIMETERS | | |
|---|---|---|---|
| | MIN | NOM | MAX |
| A | 0.70 | 0.75 | 0.80 |
| A1 | -- | -- | 0.05 |
| A3 | 0.20 REF | | |
| b | 0.27 | 0.32 | 0.37 |
| D | 3.30 BSC | | |
| D2 | 2.17 | 2.27 | 2.37 |
| E | 3.30 BSC | | |
| E2 | 1.56 | 1.66 | 1.76 |
| e | 0.65 BSC | | |
| e1 | 1.95 BSC | | |
| K | 0.90 | -- | -- |
| L | 0.30 | 0.40 | 0.50 |
| aaa | 0.10 | | |
| bbb | 0.10 | | |
| ccc | 0.10 | | |
| ddd | 0.05 | | |
| eee | 0.05 | | |

## GENERIC MARKING DIAGRAM*

XXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

| DOCUMENT NUMBER: | 98AON13672G | Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. |
|---|---|---|
| DESCRIPTION: | WDFN8 3.30x3.30x0.75, 0.65P | PAGE 1 OF 1 |

**onsemi** and onsemi are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

**onsemi**, onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent−Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as−is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## ADDITIONAL INFORMATION

**TECHNICAL PUBLICATIONS**:
**Technical Library:** www.onsemi.com/design/resources/technical−documentation
**onsemi Website:** www.onsemi.com

**ONLINE SUPPORT**: www.onsemi.com/support
**For additional information, please contact your local Sales Representative at**
www.onsemi.com/support/sales